

## Silicon NPN Power Transistors

## 2N6486 2N6487 2N6488

## DESCRIPTION

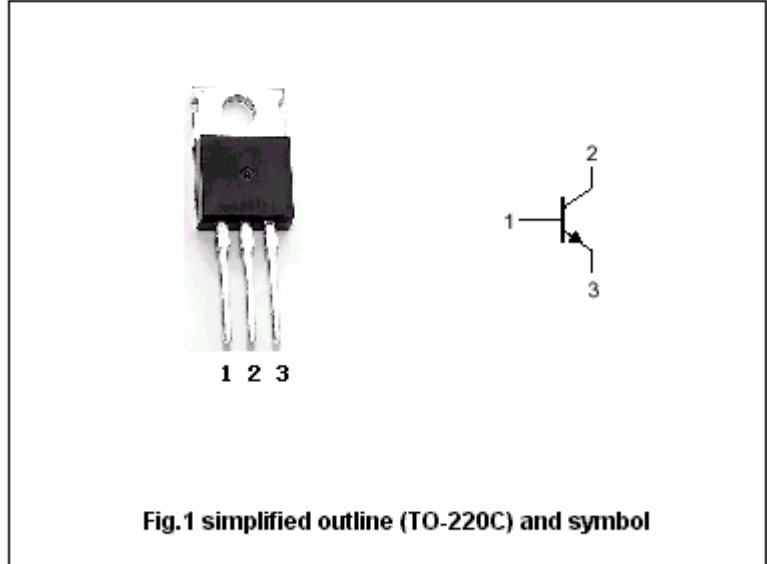
- With TO-220 package
- Excellent safe operating area
- Complement to type 2N6489 2N6490 2N6491 respectively

## APPLICATIONS

- Power amplifier and medium speed switching applications

## PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings( $T_a=25$  )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	2N6486	50	V
		2N6487	70	
		2N6488	90	
$V_{CEO}$	Collector-emitter voltage	2N6486	40	V
		2N6487	60	
		2N6488	80	
$V_{EBO}$	Emitter-base voltage	Open collector	5	V
$I_C$	Collector current		15	A
$I_B$	Base current		5	A
$P_T$	Total power dissipation	$T_C=25$	75	W
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-65~150	

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal resistance from junction to case	1.67	/W

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CE0(SUS)</sub>	Collector-emitter sustaining voltage	2N6486	I <sub>C</sub> =0.2A ; I <sub>B</sub> =0			V
		2N6487				
		2N6488				
V <sub>CEsat-1</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =5A; I <sub>B</sub> =0.5A			1.3	V
V <sub>CEsat-2</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =15A; I <sub>B</sub> =5A			3.5	V
V <sub>BE-1</sub>	Base-emitter on voltage	I <sub>C</sub> =5A ; V <sub>CE</sub> =4V			1.3	V
V <sub>BE-2</sub>	Base-emitter on voltage	I <sub>C</sub> =15A ; V <sub>CE</sub> =4V			3.5	V
I <sub>CEX</sub>	Collector cut-off current V <sub>BE</sub> =-1.5V	2N6486	V <sub>CE</sub> =45V; V <sub>CE</sub> =40V; T <sub>C</sub> =150			mA
		2N6487				
		2N6488				
I <sub>CEO</sub>	Collector cut-off current	2N6486	V <sub>CE</sub> =20V; I <sub>B</sub> =0			mA
		2N6487				
		2N6488				
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			1.0	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =5A ; V <sub>CE</sub> =4V	20		150	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =15A ; V <sub>CE</sub> =4V	5			

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PACKAGE OUTLINE



Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)